1 Scope

The present specifications shall apply to Sanken silicon diode, RM4Y.

2 Outline

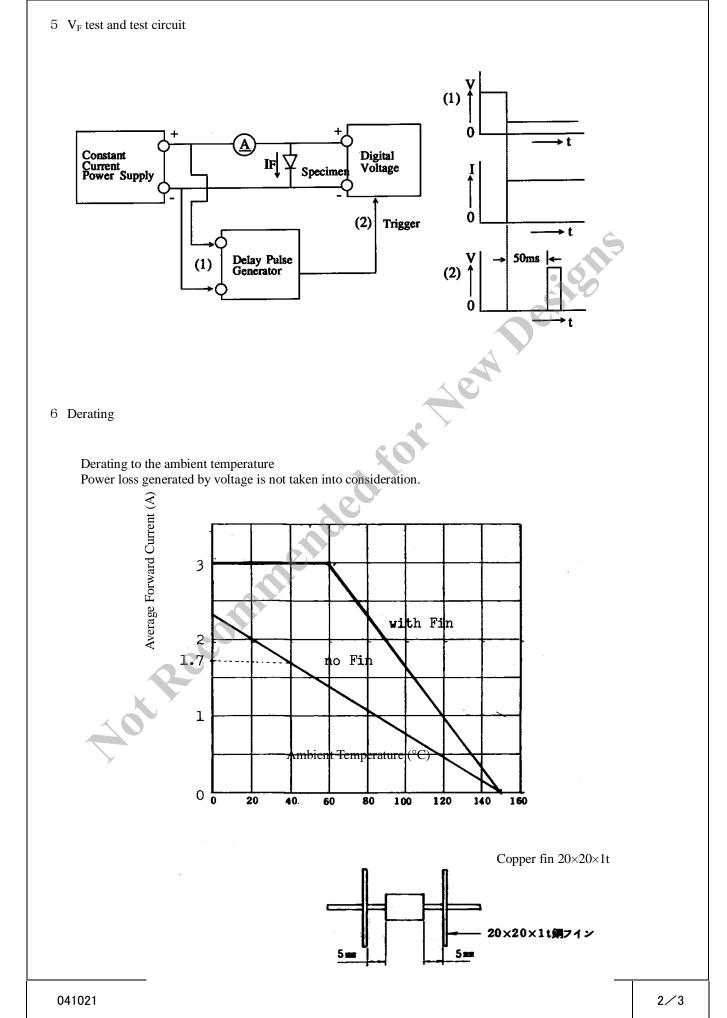
Туре	Silicon Rectifier Diode (Mesa type)			
Structure	Resin Molded Flammability: UL94V-0 (Equivalent)			
Applications	Commercial Frequency Rectification, etc.			

3 Absolute maximum ratings

Item	Symbol	Unit	Rating	Conditions	
Transient Peak Reverse Voltage	V _{RSM}	V	150		
Peak Reverse Voltage	V _{RM}	V	100		
Average Forward Current	I _{F(AV)}	А	3.0	Refer to derating curve in Section 6	
Peak Surge Forward Current	I _{FSM}	А	200	10ms. Half sine wave, one shot	
Junction Temperature	Tj	°C	-40 to +150		
Storage Temperature	T _{stg}	°C	-40 to +150		
	Transient Peak Reverse Voltage Peak Reverse Voltage Average Forward Current Peak Surge Forward Current Junction Temperature	Transient Peak Reverse Voltage V _{RSM} Peak Reverse Voltage V _{RM} Average Forward Current I _{F(AV)} Peak Surge Forward Current I _{FSM} Junction Temperature T _j	Transient Peak Reverse VoltageVPeak Reverse VoltageVRMVerage Forward CurrentIF(AV)Peak Surge Forward CurrentIFSMJunction TemperatureTj	Transient Peak Reverse Voltage V_{RSM} V 150Peak Reverse Voltage V_{RM} V 100Average Forward Current $I_{F(AV)}$ A 3.0Peak Surge Forward Current I_{FSM} A 200Junction Temperature T_j $^{\circ}$ C-40 to +150	

4 Electrical characteristics (Ta=25°C, unless otherwise specified)

No.	Item	Symbol	Unit	Rating	Conditions
1	Forward Voltage Drop	\mathbf{V}_{F}	V	0.95 max.	I _F =3.0A
2	Reverse Leakage Current	I _R	μΑ	10 max.	V _R =V _{RM}
3	Reverse Leakage Current Under High Temperature	H∙I _R	μΑ	50 max.	V _R =V _{RM} , T _j =150°C
4	Thermal Resistance	R _{th(j-l)}	°C/W	8.0 max.	Between Junction and Lead



7-1 Dimensions refer

